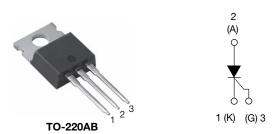


VS-25TTS...PbF Series, VS-25TTS...-M3 Series

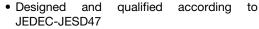
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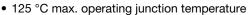
Thyristor High Voltage, Phase Control SCR, 25 A



PRODUCT SUMMARY					
Package	TO-220AB				
Diode variation	Single SCR				
I _{T(AV)}	16 A				
V_{DRM}/V_{RRM}	800 V, 1200 V				
V_{TM}	1.25 V				
I _{GT}	45 mA				
T_J	- 40 °C to 125 °C				

FEATURES





Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912





ROHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-25TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS		
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	18	22	Α		

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	16	۸			
I _{RMS}		25	A			
V _{RRM} /V _{DRM}		800/1200	V			
I _{TSM}		320	A			
V _T	16 A, T _J = 25 °C	1.25	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
T _J		- 40 to 125	°C			

VOLTAGE RATINGS					
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA		
VS-25TTS08PbF, VS-25TTS08-M3	800	800	10		
VS-25TTS12PbF, VS-25TTS12-M3	1200	1200	10		



VS-25TTS...PbF Series, VS-25TTS...-M3 Series

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ABSOLUTE MAXIMUM RATINGS							
DADAMETED	SYMBOL	DL TEST CONDITIONS		VALUES		LINUTO	
PARAMETER	SYMBOL	IESI CO	אטוווטא5	TYP.	MAX.	UNITS	
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° conduc	tion half sine wave	1	6		
Maximum RMS on-state current	I _{RMS}			2	5	Α	
Maximum peak, one-cycle,	1	10 ms sine pulse, rated \	V _{RRM} applied	27	70	^	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no volt	tage reapplied	32	20		
Maximum I ² t for fusing	I ² t	10 ms sine pulse, rated \	V _{RRM} applied	36	65	12-	
Maximum i-t for fusing	I-I	10 ms sine pulse, no voltage reapplied		515		- A ² s	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied		51	52	A²√s	
Maximum on-state voltage drop	V_{TM}	16 A, T _J = 25 °C		1.5	25	٧	
On-state slope resistance	r _t	T 405 00		12	2.0	mΩ	
Threshold voltage	V _{T(TO)}	T _J = 125 °C		1.	.0	V	
Maximum various and divest leakage accurant		T _J = 25 °C	V Datad V A/	0.	.5		
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	T _J = 125 °C	$V_R = Rated V_{RRM}/V_{DRM}$	1	0		
Holding current	I _H	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C		-	150	mA	
Maximum latching current	lι	Anode supply = 6 V, resistive load, T _J = 25 °C		20	00		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ °C, } V_{DRM} = R_g - k = Open$ 500		00	V/µs		
Maximum rate of rise of turned-on current	dl/dt	150		50	A/µs		

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}		8.0	W
Maximum average gate power	P _{G(AV)}		2.0	VV
Maximum peak positive gate current	+ I _{GM}		1.5	Α
Maximum peak negative gate voltage	- V _{GM}		10	V
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T _J = - 10 °C	60	mA
	I _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	45	
		Anode supply = 6 V, resistive load, T _J = 125 °C	20	
		Anode supply = 6 V, resistive load, T _J = - 10 °C	2.5	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	V
voltage to trigger		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V
Maximum DC gate voltage not to trigger	V_{GD}	T _J = 125 °C, V _{DRM} = Rated value		
Maximum DC gate current not to trigger	I _{GD}			mA

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9		
Typical reverse recovery time	t _{rr}	T _J = 125 °C	4	μs	
Typical turn-off time	t _q	1J = 125	110		



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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T_J , T_{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case		R_{thJC}	DC operation	1.1	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
Mounting torque -	minimum			6 (5)	kgf · cm
	maximum			12 (10)	(lbf · in)
Marking device				25TT	TS08
			Case style TO-220AB	25T1	ΓS12

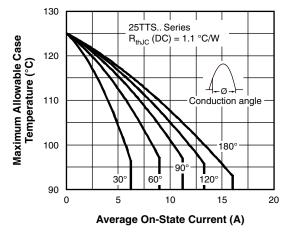


Fig. 1 - Current Rating Characteristics

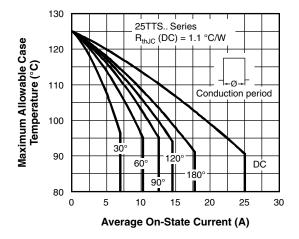


Fig. 2 - Current Rating Characteristics

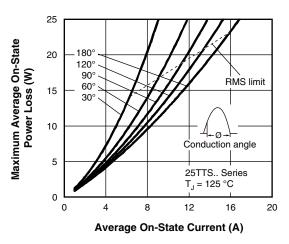


Fig. 3 - On-State Power Loss Characteristics

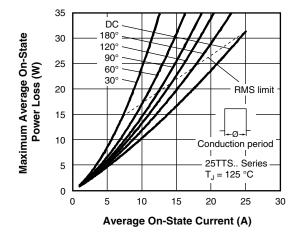


Fig. 4 - On-State Power Loss Characteristics

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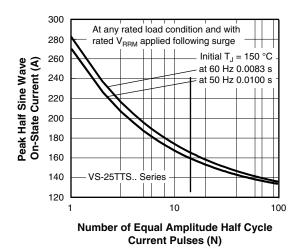


Fig. 5 - Maximum Non-Repetitive Surge Current

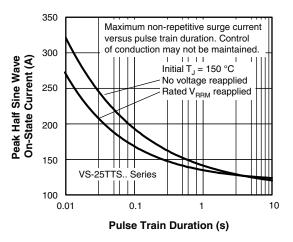


Fig. 6 - Maximum Non-Repetitive Surge Current

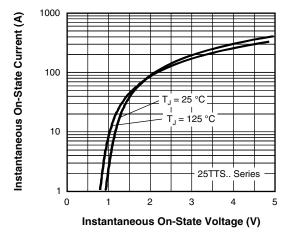


Fig. 7 - On-State Voltage Drop Characteristics

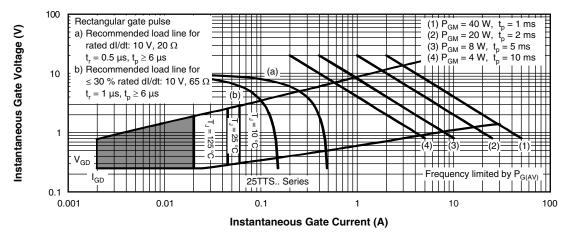


Fig. 8 - Gate Characteristics

VS-25TTS...PbF Series, VS-25TTS...-M3 Series

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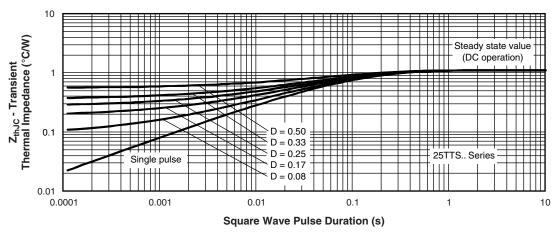
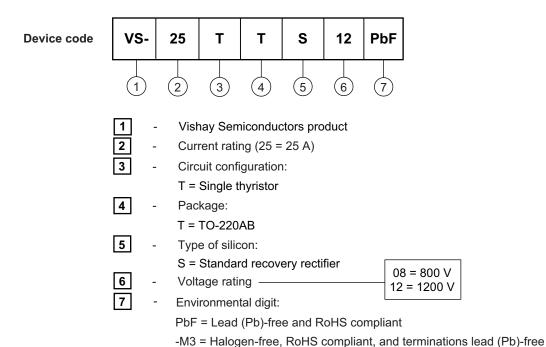


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-25TTS08PbF	50	1000	Antistatic plastic tubes		
VS-25TTS08-M3	50	1000	Antistatic plastic tubes		
VS-25TTS12PbF	50	1000	Antistatic plastic tubes		
VS-25TTS12-M3	50	1000	Antistatic plastic tubes		

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95222</u>					
Dort marking information	TO-220AB PbF	www.vishay.com/doc?95225			
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028			



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